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22. (NEW) A semiconductor device comprising:
a silicon substrate;
a MOS transistor having a gate insulating film formed on the silicon substrate, a silicon gate electrode formed on the gate insulating film, source/drain regions formed in the silicon substrate on both sides of the silicon gate electrode, and silicide layers formed on the silicon gate electrode and the source/drain regions;
an interlayer insulating film formed on the silicon substrate, covering the MOS transistor, and including a hydrogen containing film;
a wiring layer formed on the interlayer insulating film; and
a hydrogen shielding film formed on the interlayer insulating film, covering the MOS transistor and the wiring layer.

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23. (NEW) The semiconductor device according to claim 22, wherein the hydrogen-containing film contains hydrogen silsesquioxane resin.

24. (NEW) The semiconductor device according to claim 22, wherein the hydrogen shielding film includes a silicon nitride film.

25. (NEW) The semiconductor device according to claim 22, wherein the wiring layer includes a lamination of a Ti layer, an Al alloy layer, and a TiN layer.

26. (NEW) The semiconductor device according to claim 22, wherein the wiring layer includes a lamination of a Ti layer, an Al-Si-Cu alloy layer, and a TiN layer.

27. (NEW) The semiconductor device according to claim 22, wherein the wiring layer includes a plurality of wiring patterns, and the hydrogen shielding layer forms recessed surfaces between adjacent ones of the wiring patterns.

a! (and under) ~~28.~~ (NEW) The semiconductor device according to claim 22, wherein the interlayer insulating film constitutes a hydrogen supply path between the hydrogen-containing film and the silicon substrate under the gate insulating film.
